


FORM PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 05-720-US3	Serial No. 10/559,980
		INFORMATION DISCLOSURE STATEMENT BY APPLICANT	
		(Use several sheets if necessary)	
		Applicant: Kouvetakis, et al.	
		Filing Date: December 8, 2005	Group: 2812

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
RSP ↓	1.	US 2003-0157787 A1	August 21, 2003	Murthy, et al.			
	2.	US 2006-0134895 A1	June 22, 2006	Kouvetakis, et al.			
	3.	US 2006-0236923 A1	October 26, 2006	Kouvetakis, et al.			
	4.	US 2006-0163612-A1	July 27, 2006	Kouvetakis, et al.			
	5.	6,911,084	June 28, 2005	Kouvetakis, et al.			
	6.	5,532,183	July 2, 1996	Sugawara, et al.			
	7.	5,198,387	March 30, 1993	Tang, et al.			
	8.	5,714,415	February 3, 1998	Oguro			
	9.	6,410,434	June 25, 2002	Mani			
	10.	6,723,621	April 20, 2004	Cordone, et al.			
	11.	6,897,471	May 24, 2005	Soref, et al.			
	12.	6,441,716	August 27, 2002	Doppalapudi, et al.			

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FOREIGN PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
RSP ↓	13.	WO 2005/001902	January 6, 2005	PCT				
	14.	WO 2004/114368	December 29, 2004	PCT				
	15.	WO 2005/015609	February 17, 2005	PCT				
	16.	WO 2003/033781	April 24, 2003	PCT				
	17.	WO 2006/009171	January 26, 2006	PCT				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc).

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RSP ↓	18.	D. W. Jenkins, "Electronic properties of metastable GexSn1-x alloys", Phys. Rev. B., Vol: 36, pp. 7994-8001 (1987).
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	20.	G. He and H.A. Atwater, "Interband transitions in Sn _x Ge _{1-x} Alloys", Phys. Rev. Lett., Vol: 79(10), pp. 1937-1940 (1997).

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RSP	21.	O. Gurdal, R. Desjardins, J. R. A. Carlsson, N. Taylor, H. H. Radamson, J.-E. Sundgren, and J. E. Greene, "Low-temperature growth and critical epitaxial thicknesses of fully strained metastable Ge _{1-x} Sn _x (x ≤ 0.26) alloys", J. Appl. Phys., Vol: 83(1), pp. 162-170 (1998).
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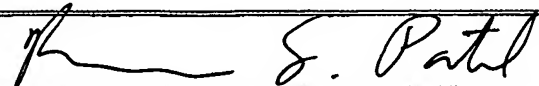
RSP ↓	31.	J. Taraci, S. Zollner, M. R. McCartney, J. Menéndez, M. A. Santana, D. J. Smith, A. Haaland, A. V. Tutukin, G. Gundersen, G. Wolf, and J. Kouvetakis, "Synthesis of silicon-based infrared semiconductors in the Ge-Sn system using molecular chemistry methods", J. of the Am. Chem. Soc., Col: 123(44), pp. 10980-10987 (2001).
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RSP	39.	T G. Kresse and J. Hafner, "Ab initio molecular dynamics for liquid metals", Phys. Rev. B47(1), pp. R558-561 (1993).
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RSP	49.	E. A. V. Ebsworth, D. J. Hutchison, D. W. H. Rankin, "The Preparation, properties, and Gas-Phase Molecular-Structure of 1,1- Difluoro-2,2-Digermylbiphosphone", J. Chem. Res., Synop, 12, pp. 393, (1980).
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RSP	59.	G. Davidson, L. A. Woodward, E. A. V. Ebsworth, G. M. Sheldrick, "The vibrational spectra and structure of trisilylarsine and trisilylstibine", Spectrochim. Acta, Part A, Vol: 23, pp. 2609-2616, (1967).
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✓	69.	A. W. Bett, F. Dimroth, G. Stollwerck, and O. V. Sulima, "III-V compounds for solar cell applications", Appl. Phys. A: materials Science & Processing, Vol: 69(2), pp. 119-129 (1999).

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RSP	70.	R. Gaska, A. Zukauskas, M. S. Shur, and M. A. Khan, "Progress in III-nitride based white light sources", Proceedings of the SPIE, Vol: 4776, pp. 82-96 (2002).
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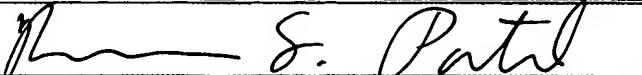
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RSP	91.	Mao R. W., et al., "Fabrication of 1.55 μ m Si-Based Resonant Cavity Enhanced Photodetectors Using Sol-Gel Bonding" IEEE Photonics Technology Letters 16(8), pp. 1930-1932 (2004).
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FORM PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 05-720-US3	Serial No. 10/559,980
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant: Kouvetakis, et al.	
		Filing Date: December 8, 2005	Group: 2812

RSP	101.	Temkin, et al., "GexSi1-x strained-layer superlattice waveguide photodetectors operating near 1.3 μ m", Appl. Phys. Lett., Vol: 48(15), pp. 963-965 (1986).
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EXAMINER <i>R. S. Patel</i>	DATE CONSIDERED 03/17/07
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RSP	112.	H. Schumann et al., "Eine einfache Methode zur Synthese von Organosilylphosphinen", J. Organometallic Chem. Vol: 55, pp. 257-260 (1973).
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EXAMINER <i>J. Patel</i>	DATE CONSIDERED 03/14/07
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		Kouvetakis, et al.	
		Filing Date:	Group:
		December 8, 2005	2812

COMMONLY OWNED CO-PENDING APPLICATIONS

Examiner Initial		
RSP	1.	Kouvetakis, et al., U.S. Patent Application No. 10/559,981, Filed on December 8, 2005.
RSP	2.	Kouvetakis, et al., U.S. Patent Application No. 10/559,979, Filed on December 8, 2005.

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